

CLEANING SOLUTION AND METHOD FOR SELECTIVELY REMOVING LAYERS IN A SILICIDATION PROCESS

ABSTRACT OF THE DISCLOSURE

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A cleaning solution selectively removes a titanium nitride layer and a non-reacting metal layer. The cleaning solution includes an acid solution and an oxidation agent with iodine. The cleaning solution also effectively removes a photoresist layer and organic materials. Moreover, the cleaning solution can be employed in tungsten gate electrode technologies that have been spotlighted because of the capability to improve device operation characteristics.

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